

A6-~~cancel~~ electrode member 24 by etching for one minute."

---

Please ~~cancel~~ claims 1-9 without prejudice or disclaimer of the subject matter contained therein.

Please ~~add~~ claims 10-15 as follows:

---

--10. A method of forming a conductive path in a semiconductor device, the conductive path to extend from an upper surface of an insulating layer of silicon dioxide formed on a silicon substrate to a conductive member embedded in the insulating layer, the method comprising:

forming an etching mask on the insulating layer, the etching mask having an opening over the conductive member and the opening being misaligned to include an offset portion extending beyond the conductive member;

A7 etching a hole in the insulating layer to the conductive member using the etching mask and a reactive gas, the hole including a misalignment groove in the insulating layer at a side of the conductive member that corresponds to the offset portion of the opening in the etching mask;

stopping a downward extension of said etching of the misalignment groove by using a polymeric product as an etch stop, the polymeric product generated by a polymeric film generating action of the reactive gas during said etching; and

filling the hole and the misalignment groove with a conductive material to form the conductive path.

11. The method of forming a conductive path of claim 10, wherein the reactive gas during said etching is a compound gas of  $\text{CHF}_3/\text{CO}$  having a flow ratio of about 15/85.

A7 Cont  
12. The method of forming a conductive path of claim 11, wherein said etching is performed in a reaction chamber at a reaction chamber pressure not less than 100mTorr and a high-frequency power of 1600W, and the offset portion is not more than  $0.04\mu\text{m}$ .

13. The method of forming a conductive path of claim 12, wherein flow rates of the  $\text{CHF}_3$  gas and the CO gas during said etching are respectively about 30 sccm and about 170 sccm.

14. The method of forming a conductive path of claim 11, wherein a flow rate of the reactive gas during said etching is not less than about 300 sccm,

said etching is performed in a reaction chamber at a reaction pressure not less than 200mTorr, and the offset portion is not more than  $0.1\mu\text{m}$ .

*Amend*

15. The method of forming a conductive path of claim 14, wherein flow rates of the CHF<sub>3</sub> gas and the CO gas during said etching are respectively about 45 sccm and about 255 sccm.--

---